Diode Semiconductor Device - Page 1 of 1



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Inclosure Material: Metal **Overall Length:** 0.310 millimeters **Overall Height:** 0.130 millimeters **Overall Width:** 0.310 millimeters **Mounting Facility Quantity:** 1 **Mounting Method:** Terminal Semiconductor Material: Silicon Voltage Rating In Volts Per Characteristic: 75.0 breakdown voltage, collector to emitter, sustained and 75.0 breakdown voltage, collector-to-base, emitter open **Current Rating Per Characteristic:** 10.00 nanoamperes forward current, average peak **Power Rating Per Characteristic:** 200.0 watts small-signal input power, common-emitter absolute Maximum Operating Tempurature Per Measurement Point: -65.0 degrees celsius case and 175.0 degrees celsius case **Special Features:** Hardness critical item **Terminal Type And Quantity:** 1 uninsulated wire lead Shelf Life: N/a Unit Of Measure: --**Demilitarization:** No Fiig: A110a0